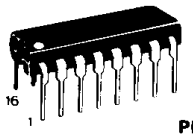
MC14578

Advance Information

Micro-Power Comparator plus Voltage Follower
CMOS



P SUFFIX
PLASTIC DIP
CASE 648

D SUFFIX
SOG
CASE 751B

ORDERING INFORMATION

MC14578P	Plastic DIP
MC14578D	SOG Package

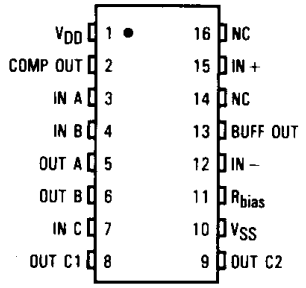
The MC14578 is an analog building block consisting of a very-high input impedance comparator. The voltage follower allows monitoring the noninverting input of the comparator without loading.

Four enhancement-mode MOSFETs are also included on chip. These FETs can be externally configured as open-drain or totem-pole outputs. The drains have on-chip static-protecting diodes. Therefore, the output voltage must be maintained between V_{SS} and V_{DD}.

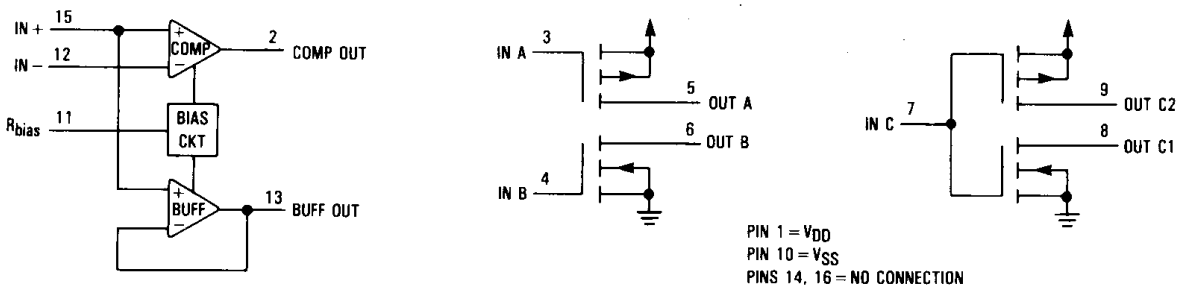
The chip requires one external component. A 3.9 MΩ ± 10% resistor must be connected from the R_{bias} pin to V_{DD}.

- Applications:
  - Pulse Shapers
  - Threshold Detectors
  - Low-Battery Detectors
  - Line-Powered Smoke Detectors
  - Liquid/Moisture Sensors
- DIP Complies with the UL217 and UL268 Specifications
- Operating Voltage Range: 3.5 to 14 V
- Operating Temperature Range: −30° to 70°C
- Input Current (IN + Pin): ±1 pA @ 25°C (DIP Only)
- Quiescent Current: 10 μA @ 25°C
- Electrostatic Discharge (ESD) Protection Circuitry on All Pins
- Chip Complexity: 26 FETs

PIN ASSIGNMENT



LOGIC DETAIL



PIN 1 = V_{DD}
PIN 10 = V_{SS}
PINS 14, 16 = NO CONNECTION

This document contains information on a new product. Specifications and information herein are subject to change without notice.

MAXIMUM RATINGS* (Voltage Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage	−0.5 to +14.0	V
V_{in}	DC Input Voltage	−0.5 to V_{DD}+0.5	V
V_{out}	DC Output Voltage	−0.5 to V_{DD}+0.5	V
I_{in}	DC Input Current, Except IN+	±10	mA
I_{in}	DC Input Current, IN+	±1	mA
I_{out}	DC Output Current, per Pin	±25	mA
I_{DD}	DC Supply Current, V_{DD} and V_{SS} Pins	±50	mA
P_D	Power Dissipation, per Package	500	mW
T_{stg}	Storage Temperature	−65 to +150	°C
T_L	Lead Temperature (10-Second Soldering)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

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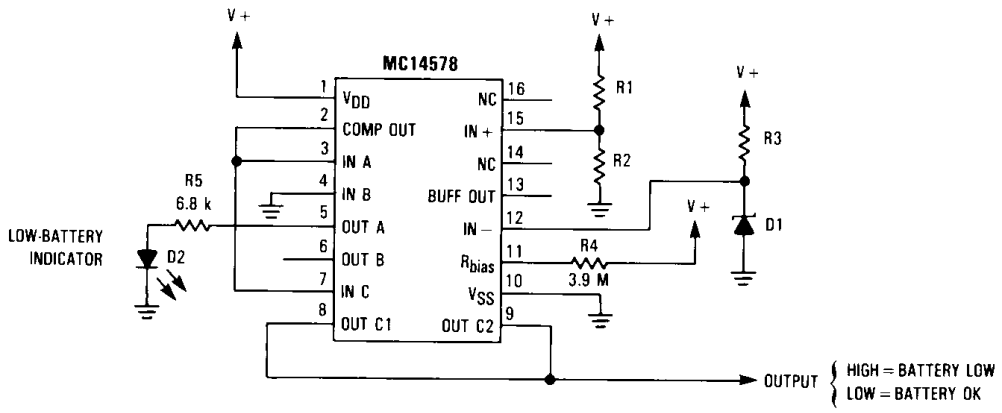
ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS}, R_{bias} = 3.9 MΩ to V_{DD}, T_A = −30° to 70°C Unless Otherwise Indicated)

Symbol	Parameter	Test Condition	V_{DD} V	Guaranteed Limit	Unit
V_{DD}	Power Supply Voltage Range		–	3.5 to 14.0	V
V_{IL}	Maximum Low-Level Input Voltage, MOSFETs Wired as Inverters; i.e., IN A tied to IN B, OUT A to OUT B, OUT C1 to OUT C2	V_{out} = 9.0 V, $\|I_{out}\| < 1$ μA	10.0	2.0	V
V_{IH}	Minimum High-Level Input Voltage, MOSFETs Wired as Inverters; i.e., IN A tied to IN B, OUT A to OUT B, OUT C1 to OUT C2	V_{out} = 1.0 V, $\|I_{out}\| < 1$ μA	10.0	8.0	V
V_{IO}	Comparator Input Offset Voltage	T_A = 25°C, Over Common Mode Range	10.0	±50	mV
		T_A = 0° to 50°C, Over Common Mode Range	3.5 to 14.0	±75	
V_{CM}	Comparator Common Mode Voltage Range		3.5 to 14.0	0.7 to V_{DD} − 1.5	V
V_{OL}	Maximum Low-Level Comparator Output Voltage	IN+: $V_{in} = V_{SS}$, IN−: $V_{in} = V_{DD}$, I_{out} = 30 μA	10.0	0.5	V
V_{OH}	Minimum High-Level Comparator Output Voltage	IN+: $V_{in} = V_{DD}$, IN−: $V_{in} = V_{SS}$, I_{out} = −30 μA	10.0	9.5	V
V_{OO}	Buffer Amp Output Offset Voltage	R_{load} = 10 MΩ to V_{DD} or V_{SS}, Over Common Mode Range	–	±100	mV
V_{OL}	Maximum Low-Level Output Voltage, MOSFETs Wired as Inverters; i.e., IN A tied to IN B, OUT A to OUT B, OUT C1 to OUT C2	OUT C1, OUT C2: I_{out} = 1.1 mA	10.0	0.5	V
		OUT A, OUT B: I_{out} = 270 μA	10.0	0.5	
V_{OH}	Minimum High-Level Output Voltage, MOSFETs Wired as Inverters; i.e., IN A tied to IN B, OUT A to OUT B, OUT C1 to OUT C2	OUT C1, OUT C2: I_{out} = −1.1 mA	10.0	9.5	V
		OUT A, OUT B: I_{out} = −270 μA	10.0	9.5	
I_{in}	Maximum Input Leakage Current — IN+ (DIP Only)	T_A = 25°C, 40% R.H., $V_{in} = V_{SS}$ or V_{DD}	10.0	±1	pA
	IN+ (DIP Only)	T_A = 50°C, $V_{in} = V_{SS}$ or V_{DD}	10.0	±6	
	IN+ (SOG), IN A, IN B, IN C, IN−	$V_{in} = V_{SS}$ or V_{DD}	10.0	±40	nA
I_{OZ}	Maximum Off-State MOSFET Leakage Current	IN A, IN C: $V_{in} = V_{DD}$, OUT A, OUT C2: $V_{out} = V_{SS}$ or V_{DD}	10.0	±100	nA
		IN B, IN C: $V_{in} = V_{SS}$, OUT B, OUT C1: $V_{out} = V_{SS}$ or V_{DD}	10.0	±100	
I_{DD}	Maximum Quiescent Current	T_A = 25°C, IN A, IN B, IN C: $V_{in} = V_{SS}$ or V_{DD}, $\|V_{IN+} - V_{IN-}\|$ = 100 mV, I_{out} = 0 μA	10.0	10	μA
C_{in}	Maximum Input Capacitance — IN+	f = 1 kHz	–	5	pF
	Other Inputs		–	15	

APPLICATIONS INFORMATION



NOTE: IN+ and IN− have very-high input impedance. Interconnect to these pins should be as short as possible.

Figure 1. Low-Battery Detector

EXAMPLE VALUES

D1: 1N4683 Zener Diode (Available From Motorola)

D2: HLMP-D150, HLMP-K150, or HLMP-Q150 Low-Current LED (Hewlett-Packard Part Number or Equivalent)

R1	R2	R3	Nominal Trip Point
470 kΩ	1.3 MΩ	20 kΩ	4.08 V
820 kΩ	1.2 MΩ	39 kΩ	5.05 V
1.2 MΩ	1.2 MΩ	62 kΩ	6.00 V

Near the switchpoint, the comparator output in the circuit of Figure 1 may chatter or oscillate. This oscillation appears on the signal labelled OUTPUT. In come cases, the oscillation in the transition region will not cause problems. For example, an MPU reading OUTPUT could sample the signal two or three times to ensure a solid level is attained. But, in a low battery detector, this probably is not necessary.

To eliminate comparator chatter, hysteresis can be added as shown in Figure 2. The circuit of Figure 2 requires slightly more operating current than the Figure 1 arrangement.

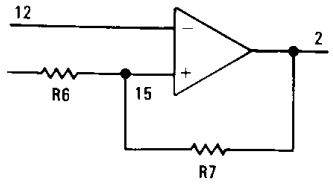


Figure 2. Adding Hysteresis